

BZT52H series

Single Zener diodes in a SOD123F package

Rev. 3 — 7 December 2010

Product data sheet

1. Product profile

1.1 General description

General-purpose Zener diodes in a SOD123F small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Total power dissipation: ≤ 830 mW
- Wide working voltage range: nominal 2.4 V to 75 V (E24 range)
- Small plastic package suitable for surface-mounted design
- Low differential resistance
- AEC-Q101 qualified

1.3 Applications

- General regulation functions

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 10$ mA	[1] -	-	0.9	V
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[2] -	-	375	mW
			[3] -	-	830	mW

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode [1]		
2	anode		

006aaa152

[1] The marking bar indicates the cathode.



3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BZT52H-B2V4 to BZT52H-C75 ^[1]	-	plastic surface-mounted package; 2 leads	SOD123F

[1] The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

4. Marking

Table 4. Marking codes

Type number	Marking code	Type number	Marking code	Type number	Marking code	Type number	Marking code
BZT52H-B2V4	DC	BZT52H-B15	DX	BZT52H-C2V4	B3	BZT52H-C15	BN
BZT52H-B2V7	DD	BZT52H-B16	DY	BZT52H-C2V7	B4	BZT52H-C16	BP
BZT52H-B3V0	DE	BZT52H-B18	DZ	BZT52H-C3V0	B5	BZT52H-C18	BQ
BZT52H-B3V3	DF	BZT52H-B20	E1	BZT52H-C3V3	B6	BZT52H-C20	BR
BZT52H-B3V6	DG	BZT52H-B22	E2	BZT52H-C3V6	B7	BZT52H-C22	BS
BZT52H-B3V9	DH	BZT52H-B24	E3	BZT52H-C3V9	B8	BZT52H-C24	BT
BZT52H-B4V3	DJ	BZT52H-B27	E4	BZT52H-C4V3	B9	BZT52H-C27	BU
BZT52H-B4V7	DK	BZT52H-B30	E5	BZT52H-C4V7	BA	BZT52H-C30	BV
BZT52H-B5V1	DL	BZT52H-B33	E6	BZT52H-C5V1	BB	BZT52H-C33	BW
BZT52H-B5V6	DM	BZT52H-B36	E7	BZT52H-C5V6	BC	BZT52H-C36	BX
BZT52H-B6V2	DN	BZT52H-B39	E8	BZT52H-C6V2	BD	BZT52H-C39	BY
BZT52H-B6V8	DP	BZT52H-B43	E9	BZT52H-C6V8	BE	BZT52H-C43	BZ
BZT52H-B7V5	DQ	BZT52H-B47	EA	BZT52H-C7V5	BF	BZT52H-C47	C1
BZT52H-B8V2	DR	BZT52H-B51	EB	BZT52H-C8V2	BG	BZT52H-C51	C2
BZT52H-B9V1	DS	BZT52H-B56	EC	BZT52H-C9V1	BH	BZT52H-C56	C3
BZT52H-B10	DT	BZT52H-B62	ED	BZT52H-C10	BJ	BZT52H-C62	C4
BZT52H-B11	DU	BZT52H-B68	EE	BZT52H-C11	BK	BZT52H-C68	C5
BZT52H-B12	DV	BZT52H-B75	EF	BZT52H-C12	BL	BZT52H-C75	C6
BZT52H-B13	DW	-	-	BZT52H-C13	BM	-	-

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_F	forward current		-	250	mA
I_{ZSM}	non-repetitive peak reverse current		-	see Table 8, 9 and 10	
P_{ZSM}	non-repetitive peak reverse power dissipation		[1] -	40	W
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2] -	375	mW
			[3] -	830	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ °C}$ prior to surge.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	330	K/W
			[2] -	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[3] -	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

[3] Soldering point of cathode tab.

7. Characteristics

Table 7. Characteristics

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 10\text{ mA}$	[1]	-	0.9	V

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

Table 8. Characteristics per type; BZT52H-B2V4 to BZT52H-C24

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZT52H -xxx	Sel	Working voltage V_Z (V); $I_Z = 5\text{ mA}$		Maximum differential resistance r_{dif} (Ω)		Reverse current I_R (μA)		Temperature coefficient S_Z (mV/K); $I_Z = 5\text{ mA}$		Diode capacitance C_d (pF)[1]	Non-repetitive peak reverse current I_{ZSM} (A)[2]
		Min	Max	$I_Z = 1\text{ mA}$	$I_Z = 5\text{ mA}$	Max	V_R (V)	Min	Max	Max	Max
2V4	B	2.35	2.45	400	85	50	1	-3.5	0.0	450	6.0
	C	2.2	2.6								
2V7	B	2.65	2.75	500	83	20	1	-3.5	0.0	450	6.0
	C	2.5	2.9								
3V0	B	2.94	3.06	500	95	10	1	-3.5	0.0	450	6.0
	C	2.8	3.2								
3V3	B	3.23	3.37	500	95	5	1	-3.5	0.0	450	6.0
	C	3.1	3.5								
3V6	B	3.53	3.67	500	95	5	1	-3.5	0.0	450	6.0
	C	3.4	3.8								
3V9	B	3.82	3.98	500	95	3	1	-3.5	0.0	450	6.0
	C	3.7	4.1								
4V3	B	4.21	4.39	500	95	3	1	-3.5	0.0	450	6.0
	C	4.0	4.6								
4V7	B	4.61	4.79	500	78	3	2	-3.5	0.2	300	6.0
	C	4.4	5.0								
5V1	B	5.0	5.2	480	60	2	2	-2.7	1.2	300	6.0
	C	4.8	5.4								
5V6	B	5.49	5.71	400	40	1	2	-2.0	2.5	300	6.0
	C	5.2	6.0								
6V2	B	6.08	6.32	150	10	3	4	0.4	3.7	200	6.0
	C	5.8	6.6								
6V8	B	6.66	6.94	80	8	2	4	1.2	4.5	200	6.0
	C	6.4	7.2								
7V5	B	7.35	7.65	80	10	1	5	2.5	5.3	150	4.0
	C	7.0	7.9								
8V2	B	8.04	8.36	80	10	0.7	5	3.2	6.2	150	4.0
	C	7.7	8.7								

Table 8. Characteristics per type; BZT52H-B2V4 to BZT52H-C24 ...continued

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZT52H -xxx	Sel	Working voltage V_Z (V); $I_Z = 5\text{ mA}$		Maximum differential resistance r_{dif} (Ω)		Reverse current I_R (μA)		Temperature coefficient S_Z (mV/K); $I_Z = 5\text{ mA}$		Diode capacitance C_d (pF) ^[1]	Non-repetitive peak reverse current I_{ZSM} (A) ^[2]
		Min	Max	$I_Z = 1\text{ mA}$	$I_Z = 5\text{ mA}$	Max	V_R (V)	Min	Max	Max	Max
9V1	B	8.92	9.28	100	10	0.5	6	3.8	7.0	150	3.0
	C	8.5	9.6								
10	B	9.8	10.2	70	10	0.2	7	4.5	8.0	90	3.0
	C	9.4	10.6								
11	B	10.8	11.2	70	10	0.1	8	5.4	9.0	85	2.5
	C	10.4	11.6								
12	B	11.8	12.2	90	10	0.1	8	6.0	10.0	85	2.5
	C	11.4	12.7								
13	B	12.7	13.3	110	10	0.1	8	7.0	11.0	80	2.5
	C	12.4	14.1								
15	B	14.7	15.3	110	15	0.05	10.5	9.2	13.0	75	2.0
	C	13.8	15.6								
16	B	15.7	16.3	170	20	0.05	11.2	10.4	14.0	75	1.5
	C	15.3	17.1								
18	B	17.6	18.4	170	20	0.05	12.6	12.4	16.0	70	1.5
	C	16.8	19.1								
20	B	19.6	20.4	220	20	0.05	14	14.4	18.0	60	1.5
	C	18.8	21.2								
22	B	21.6	22.4	220	25	0.05	15.4	16.4	20.0	60	1.25
	C	20.8	23.3								
24	B	23.5	24.5	220	30	0.05	16.8	18.4	22.0	55	1.25
	C	22.8	25.6								

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$.[2] $t_p = 100\text{ }\mu\text{s}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$.

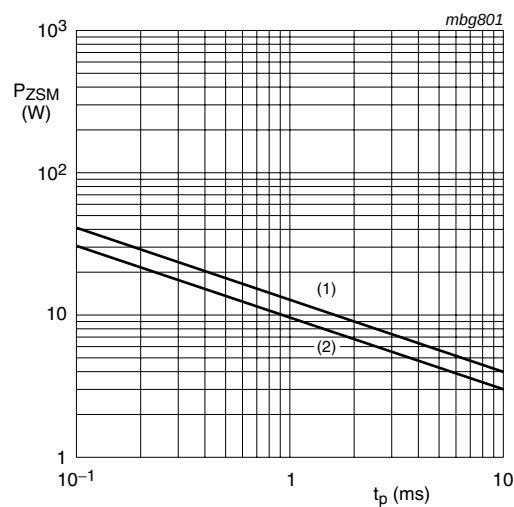
Table 9. Characteristics per type; BZT52H-B27 to BZT52H-C51 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZT52H -xxx	Sel	Working voltage V_Z (V); $I_Z = 2\text{ mA}$		Maximum differential resistance r_{dif} (Ω)		Reverse current I_R (μA)		Temperature coefficient S_Z (mV/K); $I_Z = 5\text{ mA}$		Diode capacitance C_d (pF) ^[1]	Non-repetitive peak reverse current I_{ZSM} (A) ^[2]
		Min	Max	$I_Z = 1\text{ mA}$	$I_Z = 5\text{ mA}$	Max	V_R (V)	Min	Max	Max	Max
27	B	26.5	27.5	250	40	0.05	18.9	21.4	25.3	50	1.0
	C	25.1	28.9								
30	B	29.4	30.6	250	40	0.05	21	24.4	29.4	50	1.0
	C	28.0	32.0								
33	B	32.3	33.7	250	40	0.05	23.1	27.4	33.4	45	0.9
	C	31.0	35.0								
36	B	35.3	36.7	250	60	0.05	25.2	30.4	37.4	45	0.8
	C	34.0	38.0								
39	B	38.2	39.8	300	75	0.05	27.3	33.4	41.2	45	0.7
	C	37.0	41.0								
43	B	42.1	43.9	325	80	0.05	30.1	37.6	46.6	40	0.6
	C	40.0	46.0								
47	B	46.1	47.9	325	90	0.05	32.9	42.0	51.8	40	0.5
	C	44.0	50.0								
51	B	50.0	52.0	350	100	0.05	35.7	46.6	57.2	40	0.4
	C	48.0	54.0								

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$.[2] $t_p = 100\text{ }\mu\text{s}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$.**Table 10. Characteristics per type; BZT52H-B56 to BZT52H-C75** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

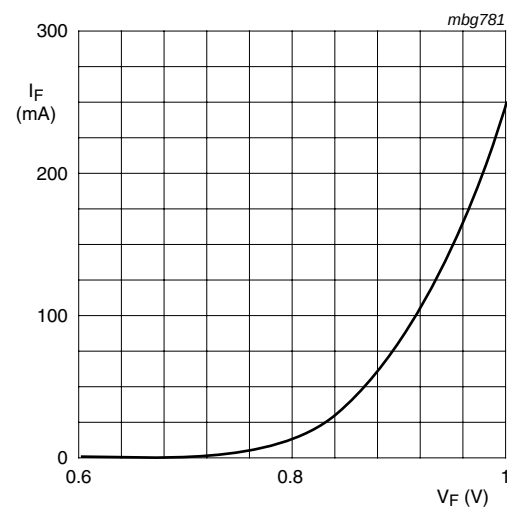
BZT52H -xxx	Sel	Working voltage V_Z (V); $I_Z = 2\text{ mA}$		Maximum differential resistance r_{dif} (Ω)		Reverse current I_R (μA)		Temperature coefficient S_Z (mV/K); $I_Z = 5\text{ mA}$		Diode capacitance C_d (pF) ^[1]	Non-repetitive peak reverse current I_{ZSM} (A) ^[2]
		Min	Max	$I_Z = 0.5\text{ mA}$	$I_Z = 2\text{ mA}$	Max	V_R (V)	Min	Max	Max	Max
56	B	54.9	57.1	375	120	0.05	39.2	52.2	63.8	40	0.3
	C	52.0	60.0								
62	B	60.8	63.2	400	140	0.05	43.4	58.8	71.6	35	0.3
	C	58.0	66.0								
68	B	66.6	69.4	400	160	0.05	47.6	65.6	79.8	35	0.25
	C	64.0	72.0								
75	B	73.5	76.5	400	175	0.05	52.5	73.4	88.6	35	0.20
	C	70.0	79.0								

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$.[2] $t_p = 100\text{ }\mu\text{s}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$.



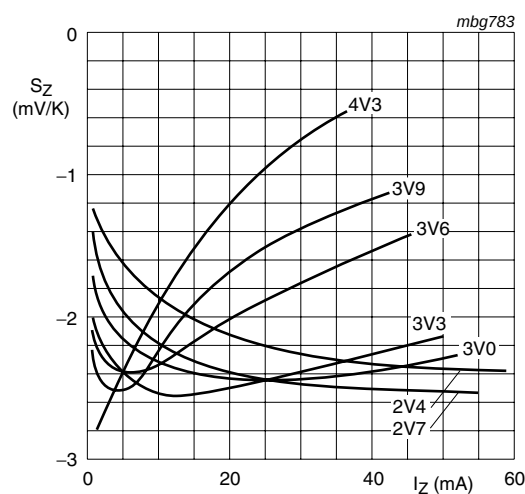
- (1) $T_j = 25^\circ\text{C}$ (prior to surge)
- (2) $T_j = 150^\circ\text{C}$ (prior to surge)

Fig 1. Non-repetitive peak reverse power dissipation as a function of pulse duration; maximum values



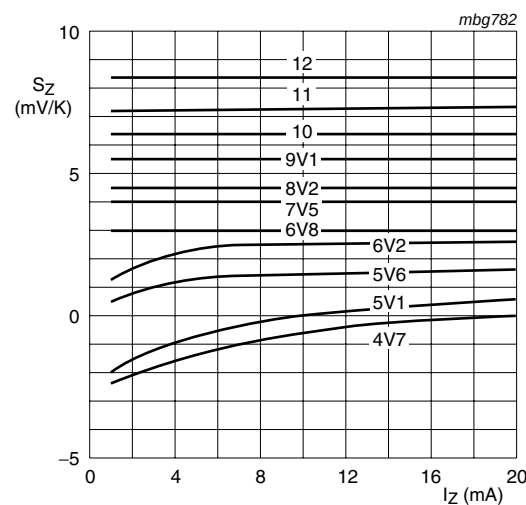
$T_j = 25^\circ\text{C}$

Fig 2. Forward current as a function of forward voltage; typical values



BZT52H-B/C2V4 to BZT52H-B/C4V3
 $T_j = 25^\circ\text{C}$ to 150°C

Fig 3. Temperature coefficient as a function of working current; typical values



BZT52H-B/C4V7 to BZT52H-B/C12
 $T_j = 25^\circ\text{C}$ to 150°C

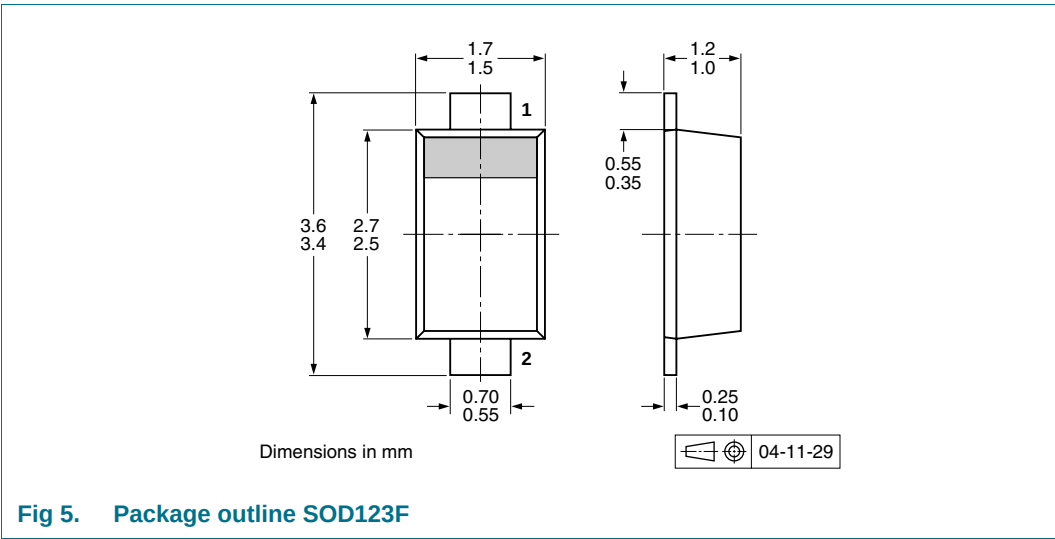
Fig 4. Temperature coefficient as a function of working current; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

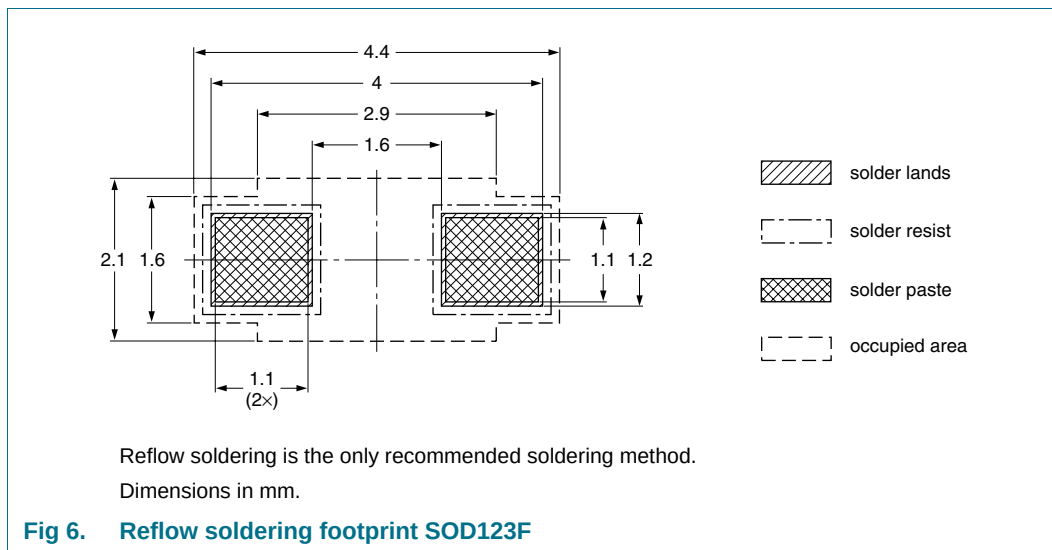
Table 11. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[\[1\]](#)

Type number	Package	Description	Packing quantity	
			3000	10000
BZT52H-B2V4 to BZT52H-C75	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering



12. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BZT52H_SER v.3	20101207	Product data sheet	-	BZT52H_SER v.2
Modifications:	• Added selection B. • Section 1.2 "Features and benefits": amended. • Table 2 "Pinning": graphic symbol updated. • Section 8 "Test information": added. • Section 13 "Legal information": updated.			
BZT52H_SER v.2	20091115	Product data sheet	-	BZT52H_SER v.1
BZT52H_SER v.1	20051222	Product data sheet	-	-